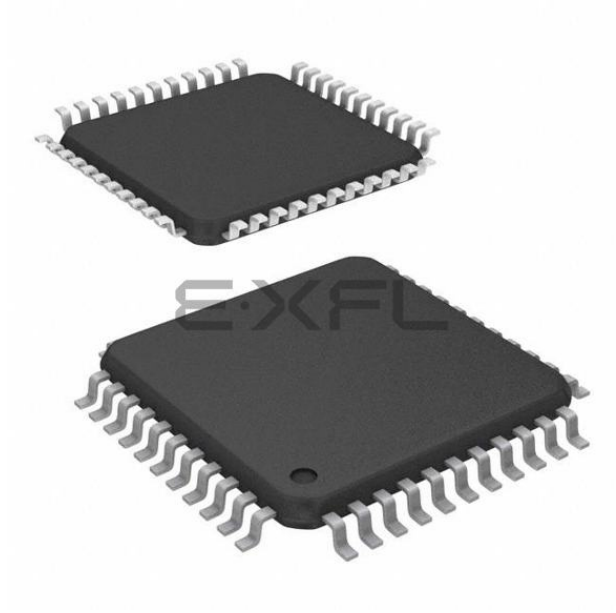

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M0+
Core Size	32-Bit Single-Core
Speed	24MHz
Connectivity	I²C, IrDA, LINbus, Microwire, SmartCard, SPI, SSP, UART/USART
Peripherals	Brown-out Detect/Reset, CapSense, LCD, LVD, POR, PWM, WDT
Number of I/O	36
Program Memory Size	32KB (32K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.71V ~ 5.5V
Data Converters	A/D 16x10b Slope, 16x12b SAR; D/A 2xIDAC
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	44-LQFP
Supplier Device Package	44-TQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/infineon-technologies/cy8c4125axi-s423

supports EZI2C that creates a mailbox address range in the memory of the PSoC 4100S and effectively reduces I^2C communication to reading from and writing to an array in memory. In addition, the block supports an 8-deep FIFO for receive and transmit which, by increasing the time given for the CPU to read data, greatly reduces the need for clock stretching caused by the CPU not having read data on time.

The I^2C peripheral is compatible with the I^2C Standard-mode and Fast-mode devices as defined in the NXP I^2C-bus specification and user manual (UM10204). The I^2C bus I/O is implemented with GPIO in open-drain modes.

The PSoC 4100S is not completely compliant with the I^2C spec in the following respect:

- GPIO cells are not overvoltage tolerant and, therefore, cannot be hot-swapped or powered up independently of the rest of the I^2C system.

UART Mode: This is a full-feature UART operating at up to 1 Mbps. It supports automotive single-wire interface (LIN), infrared interface (IrDA), and SmartCard (ISO7816) protocols, all of which are minor variants of the basic UART protocol. In addition, it supports the 9-bit multiprocessor mode that allows addressing of peripherals connected over common RX and TX lines. Common UART functions such as parity error, break detect, and frame error are supported. An 8-deep FIFO allows much greater CPU service latencies to be tolerated.

SPI Mode: The SPI mode supports full Motorola SPI, TI SSP (adds a start pulse used to synchronize SPI Codecs), and National Microwire (half-duplex form of SPI). The SPI block can use the FIFO.

GPIO

The PSoC 4100S has up to 36 GPIOs. The GPIO block implements the following:

- Eight drive modes:
  - Analog input mode (input and output buffers disabled)
  - Input only
  - Weak pull-up with strong pull-down
  - Strong pull-up with weak pull-down
  - Open drain with strong pull-down
  - Open drain with strong pull-up
  - Strong pull-up with strong pull-down
  - Weak pull-up with weak pull-down
- Input threshold select (CMOS or LVTTL).
- Individual control of input and output buffer enabling/disabling in addition to the drive strength modes
- Selectable slew rates for dV/dt related noise control to improve EMI

The pins are organized in logical entities called ports, which are 8-bit in width (less for Ports 2 and 3). During power-on and reset, the blocks are forced to the disable state so as not to crowbar any inputs and/or cause excess turn-on current. A multiplexing network known as a high-speed I/O matrix is used to multiplex between various signals that may connect to an I/O pin.

Data output and pin state registers store, respectively, the values to be driven on the pins and the states of the pins themselves.

Every I/O pin can generate an interrupt if so enabled and each I/O port has an interrupt request (IRQ) and interrupt service routine (ISR) vector associated with it (5 for PSoC 4100S).

Special Function Peripherals

CapSense

CapSense is supported in the PSoC 4100S through a CapSense Sigma-Delta (CSD) block that can be connected to any pins through an analog multiplex bus via analog switches. CapSense function can thus be provided on any available pin or group of pins in a system under software control. A PSoC Creator component is provided for the CapSense block to make it easy for the user.

Shield voltage can be driven on another analog multiplex bus to provide water-tolerance capability. Water tolerance is provided by driving the shield electrode in phase with the sense electrode to keep the shield capacitance from attenuating the sensed input. Proximity sensing can also be implemented.

The CapSense block has two IDACs, which can be used for general purposes if CapSense is not being used (both IDACs are available in that case) or if CapSense is used without water tolerance (one IDAC is available).

The CapSense block also provides a 10-bit Slope ADC function which can be used in conjunction with the CapSense function.

The CapSense block is an advanced, low-noise, programmable block with programmable voltage references and current source ranges for improved sensitivity and flexibility. It can also use an external reference voltage. It has a full-wave CSD mode that alternates sensing to VDDA and ground to null out power-supply related noise.

LCD Segment Drive

The PSoC 4100S has an LCD controller, which can drive up to 4 commons and up to 32 segments. It uses full digital methods to drive the LCD segments requiring no generation of internal LCD voltages. The two methods used are referred to as Digital Correlation and PWM. Digital Correlation pertains to modulating the frequency and drive levels of the common and segment signals to generate the highest RMS voltage across a segment to light it up or to keep the RMS signal to zero. This method is good for STN displays but may result in reduced contrast with TN (cheaper) displays. PWM pertains to driving the panel with PWM signals to effectively use the capacitance of the panel to provide the integration of the modulated pulse-width to generate the desired LCD voltage. This method results in higher power consumption but can result in better results when driving TN displays. LCD operation is supported during Deep Sleep refreshing a small display buffer (4 bits; 1 32-bit register per port).

Pinouts

The following table provides the pin list for PSoC 4100S for the 48-pin TQFP, 44-pin TQFP, 40-pin QFN, 32-pin QFN, and 35-ball CSP packages. All port pins support GPIO.

Table 1. Pin List

48-TQFP		44-TQFP		40-QFN		32-QFN		35-CSP	
Pin	Name	Pin	Name	Pin	Name	Pin	Name	Pin	Name
28	P0.0	24	P0.0	22	P0.0	17	P0.0	C3	P0.0
29	P0.1	25	P0.1	23	P0.1	18	P0.1	A5	P0.1
30	P0.2	26	P0.2	24	P0.2	19	P0.2	A4	P0.2
31	P0.3	27	P0.3	25	P0.3	20	P0.3	A3	P0.3
32	P0.4	28	P0.4	26	P0.4	21	P0.4	B3	P0.4
33	P0.5	29	P0.5	27	P0.5	22	P0.5	A6	P0.5
34	P0.6	30	P0.6	28	P0.6	23	P0.6	B4	P0.6
35	P0.7	31	P0.7	29	P0.7			B5	P0.7
36	XRES	32	XRES	30	XRES	24	XRES	B6	XRES
37	VCCD	33	VCCD	31	VCCD	25	VCCD	A7	VCCD
38	VSSD			DN	VSSD	26	VSSD	B7	VSS
39	VDDD	34	VDDD	32	VDDD			C7	VDD
40	VDDA	35	VDDA	33	VDDA	27	VDD	C7	VDD
41	VSSA	36	VSSA	34	VSSA	28	VSSA	B7	VSS
42	P1.0	37	P1.0	35	P1.0	29	P1.0	C4	P1.0
43	P1.1	38	P1.1	36	P1.1	30	P1.1	C5	P1.1
44	P1.2	39	P1.2	37	P1.2	31	P1.2	C6	P1.2
45	P1.3	40	P1.3	38	P1.3	32	P1.3	D7	P1.3
46	P1.4	41	P1.4	39	P1.4			D4	P1.4
47	P1.5	42	P1.5					D5	P1.5
48	P1.6	43	P1.6					D6	P1.6
1	P1.7/VREF	44	P1.7/VREF	40	P1.7/VREF	1	P1.7/VREF	E7	P1.7/VREF
		1	VSSD						
2	P2.0	2	P2.0	1	P2.0	2	P2.0		
3	P2.1	3	P2.1	2	P2.1	3	P2.1		
4	P2.2	4	P2.2	3	P2.2	4	P2.2	D3	P2.2
5	P2.3	5	P2.3	4	P2.3	5	P2.3	E4	P2.3
6	P2.4	6	P2.4	5	P2.4			E5	P2.4
7	P2.5	7	P2.5	6	P2.5	6	P2.5	E6	P2.5
8	P2.6	8	P2.6	7	P2.6	7	P2.6	E3	P2.6
9	P2.7	9	P2.7	8	P2.7	8	P2.7	E2	P2.7
10	VSSD	10	VSSD	9	VSSD				
12	P3.0	11	P3.0	10	P3.0	9	P3.0	E1	P3.0
13	P3.1	12	P3.1	11	P3.1	10	P3.1	D2	P3.1
14	P3.2	13	P3.2	12	P3.2	11	P3.2	D1	P3.2
16	P3.3	14	P3.3	13	P3.3	12	P3.3	C1	P3.3
17	P3.4	15	P3.4	14	P3.4			C2	P3.4
18	P3.5	16	P3.5	15	P3.5				

Table 1. Pin List *(continued)*

48-TQFP		44-TQFP		40-QFN		32-QFN		35-CSP	
Pin	**Name**	**Pin**	**Name**	**Pin**	**Name**	**Pin**	**Name**	**Pin**	**Name**
19	P3.6	17	P3.6	16	P3.6				
20	P3.7	18	P3.7	17	P3.7				
21	VDDD	19	VDDD						
22	P4.0	20	P4.0	18	P4.0	13	P4.0	B1	P4.0
23	P4.1	21	P4.1	19	P4.1	14	P4.1	B2	P4.1
24	P4.2	22	P4.2	20	P4.2	15	P4.2	A2	P4.2
25	P4.3	23	P4.3	21	P4.3	16	P4.3	A1	P4.3

Notes: Pins 11, 15, 26, and 27 are No Connects (NC) on the 48-pin TQFP.

Descriptions of the Power pins are as follows:

VDDD: Power supply for the digital section.

VDDA: Power supply for the analog section.

VSSD, VSSA: Ground pins for the digital and analog sections respectively.

VCCD: Regulated digital supply (1.8 V ±5%)

VDD: Power supply to all sections of the chip

VSS: Ground for all sections of the chip

Electrical Specifications

Absolute Maximum Ratings

Table 2. Absolute Maximum Ratings[1]

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID1	V_{DDD_ABS}	Digital supply relative to V_{SS}	–0.5	–	6	V	–
SID2	V_{CCD_ABS}	Direct digital core voltage input relative to V_{SS}	–0.5	–	1.95		–
SID3	V_{GPIO_ABS}	GPIO voltage	–0.5	–	V_{DD}+0.5		–
SID4	I_{GPIO_ABS}	Maximum current per GPIO	–25	–	25	mA	–
SID5	$I_{GPIO\_injection}$	GPIO injection current, Max for V_{IH} > V_{DDD}, and Min for V_{IL} < V_{SS}	–0.5	–	0.5		Current injected per pin
BID44	ESD_HBM	Electrostatic discharge human body model	2200	–	–	V	–
BID45	ESD_CDM	Electrostatic discharge charged device model	500	–	–		–
BID46	LU	Pin current for latch-up	–140	–	140	mA	–

Device Level Specifications

All specifications are valid for –40 °C ≤ T_A ≤ 85 °C and T_J ≤ 100 °C, except where noted. Specifications are valid for 1.71 V to 5.5 V, except where noted.

Table 3. DC Specifications

Typical values measured at V_{DD} = 3.3 V and 25 °C.

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID53	V_{DD}	Power supply input voltage	1.8	–	5.5	V	Internally regulated supply
SID255	V_{DD}	Power supply input voltage (V_{CCD} = V_{DDD} = V_{DDA})	1.71	–	1.89		Internally unregulated supply
SID54	V_{CCD}	Output voltage (for core logic)	–	1.8	–		–
SID55	C_{EFC}	External regulator voltage bypass	–	0.1	–	µF	X5R ceramic or better
SID56	C_{EXC}	Power supply bypass capacitor	–	1	–		X5R ceramic or better
Active Mode, V_{DD} = 1.8 V to 5.5 V. Typical values measured at VDD = 3.3 V and 25 °C.							
SID10	I_{DD5}	Execute from flash; CPU at 6 MHz	–	1.8	2.7	mA	Max is at 85 °C and 5.5 V
SID16	I_{DD8}	Execute from flash; CPU at 24 MHz	–	3.0	4.75		Max is at 85 °C and 5.5 V
SID19	I_{DD11}	Execute from flash; CPU at 48 MHz	–	5.4	6.85		Max is at 85 °C and 5.5 V

Note
1. Usage above the absolute maximum conditions listed in Table 2 may cause permanent damage to the device. Exposure to Absolute Maximum conditions for extended periods of time may affect device reliability. The Maximum Storage Temperature is 150 °C in compliance with JEDEC Standard JESD22-A103, High Temperature Storage Life. When used below Absolute Maximum conditions but above normal operating conditions, the device may not operate to specification.

Table 3. DC Specifications *(continued)*

Typical values measured at V_{DD} = 3.3 V and 25 °C.

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
Sleep Mode, VDDD = 1.8 V to 5.5 V (Regulator on)							
SID22	IDD17	I^2C wakeup WDT, and Comparators on	–	1.7	2.2	mA	6 MHZ. Max is at 85 °C and 5.5 V.
SID25	IDD20	I^2C wakeup, WDT, and Comparators on.	–	2.2	2.5		12 MHZ. Max is at 85 °C and 5.5 V.
Sleep Mode, V_{DDD} = 1.71 V to 1.89 V (Regulator bypassed)							
SID28	IDD23	I^2C wakeup, WDT, and Comparators on	–	0.7	0.9	mA	6 MHZ. Max is at 85 °C and 5.5 V.
SID28A	IDD23A	I^2C wakeup, WDT, and Comparators on	–	1	1.2	mA	12 MHZ. Max is at 85 °C and 5.5 V.
Deep Sleep Mode, V_{DD} = 1.8 V to 3.6 V (Regulator on)							
SID31	I_{DD26}	I^2C wakeup and WDT on	–	2.5	60	µA	Max is at 3.6 V and 85 °C.
Deep Sleep Mode, V_{DD} = 3.6 V to 5.5 V (Regulator on)							
SID34	I_{DD29}	I^2C wakeup and WDT on	–	2.5	60	µA	Max is at 5.5 V and 85 °C.
Deep Sleep Mode, V_{DD} = V_{CCD} = 1.71 V to 1.89 V (Regulator bypassed)							
SID37	I_{DD32}	I^2C wakeup and WDT on	–	2.5	65	µA	Max is at 1.89 V and 85 °C.
XRES Current							
SID307	I_{DD_XR}	Supply current while XRES asserted	–	2	5	mA	–

Table 4. AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID48	F_{CPU}	CPU frequency	DC	–	48	MHz	$1.71 \le V_{DD} \le 5.5$
SID49[3]	T_{SLEEP}	Wakeup from Sleep mode	–	0	–	µs	
SID50[3]	$T_{DEEPSLEEP}$	Wakeup from Deep Sleep mode	–	35	–		

Note
2. Guaranteed by characterization.

Table 6. GPIO AC Specifications

(Guaranteed by Characterization) *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID73	T_{FALLS}	Fall time in slow strong mode	10	–	60	–	3.3 V V_{DDD}, Cload = 25 pF
SID74	$F_{GPIOUT1}$	GPIO F_{OUT}; 3.3 V ≤ V_{DDD} ≤ 5.5 V Fast strong mode	–	–	33	MHz	90/10%, 25 pF load, 60/40 duty cycle
SID75	$F_{GPIOUT2}$	GPIO F_{OUT}; 1.71 V≤ V_{DDD}≤ 3.3 V Fast strong mode	–	–	16.7		90/10%, 25 pF load, 60/40 duty cycle
SID76	$F_{GPIOUT3}$	GPIO F_{OUT}; 3.3 V ≤ V_{DDD} ≤ 5.5 V Slow strong mode	–	–	7		90/10%, 25 pF load, 60/40 duty cycle
SID245	$F_{GPIOUT4}$	GPIO F_{OUT}; 1.71 V ≤ V_{DDD} ≤ 3.3 V Slow strong mode.	–	–	3.5		90/10%, 25 pF load, 60/40 duty cycle
SID246	F_{GPIOIN}	GPIO input operating frequency; 1.71 V ≤ V_{DDD} ≤ 5.5 V	–	–	48		90/10% V_{IO}

XRES

Table 7. XRES DC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID77	V_{IH}	Input voltage high threshold	0.7 × V_{DDD}	–	–	V	CMOS Input
SID78	V_{IL}	Input voltage low threshold	–	–	0.3 × V_{DDD}		
SID79	R_{PULLUP}	Pull-up resistor	–	60	–	kΩ	–
SID80	C_{IN}	Input capacitance	–	–	7	pF	–
SID81[5]	$V_{HYSXRES}$	Input voltage hysteresis	–	100	–	mV	Typical hysteresis is 200 mV for V_{DD} > 4.5 V
SID82	I_{DIODE}	Current through protection diode to V_{DD}/V_{SS}	–	–	100	µA	

Table 8. XRES AC Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID83[5]	$T_{RESETWIDTH}$	Reset pulse width	1	–	–	µs	–
BID194[5]	$T_{RESETWAKE}$	Wake-up time from reset release	–	–	2.7	ms	–

Note
5. Guaranteed by characterization.

Table 9. CTBm Opamp Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID299	T_OP_WAKE	From disable to enable, no external RC dominating	–	–	25	µs	–
SID299A	OL_GAIN	Open Loop Gain	–	90	–	dB	
	COMP_MODE	Comparator mode; 50 mV drive, T_{rise}=T_{fall} (approx.)					
SID300	TPD1	Response time; power=hi	–	150	–	ns	Input is 0.2 V to V_{DDA}-0.2 V
SID301	TPD2	Response time; power=med	–	500	–		Input is 0.2 V to V_{DDA}-0.2 V
SID302	TPD3	Response time; power=lo	–	2500	–		Input is 0.2 V to V_{DDA}-0.2 V
SID303	VHYST_OP	Hysteresis	–	10	–	mV	–
SID304	WUP_CTB	Wake-up time from Enabled to Usable	–	–	25	µs	–
	Deep Sleep Mode	Mode 2 is lowest current range. Mode 1 has higher GBW.					
SID_DS_1	$I_{DD\_HI\_M1}$	Mode 1, High current	–	1400	–	µA	25 °C
SID_DS_2	$I_{DD\_MED\_M1}$	Mode 1, Medium current	–	700	–		25 °C
SID_DS_3	$I_{DD\_LOW\_M1}$	Mode 1, Low current	–	200	–		25 °C
SID_DS_4	$I_{DD\_HI\_M2}$	Mode 2, High current	–	120	–		25 °C
SID_DS_5	$I_{DD\_MED\_M2}$	Mode 2, Medium current	–	60	–		25 °C
SID_DS_6	$I_{DD\_LOW\_M2}$	Mode 2, Low current	–	15	–		25 °C

Table 13. SAR Specifications *(continued)*

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details/ Conditions
SID99	A_OFFSET	Input offset voltage	–	–	2	mV	Measured with 1-V reference
SID100	A_ISAR	Current consumption	–	–	1	mA	
SID101	A_VINS	Input voltage range - single ended	V_{SS}	–	V_{DDA}	V	
SID102	A_VIND	Input voltage range - differential[	V_{SS}	–	V_{DDA}	V	
SID103	A_INRES	Input resistance	–	–	2.2	KΩ	
SID104	A_INCAP	Input capacitance	–	–	10	pF	
SID260	VREFSAR	Trimmed internal reference to SAR	–	–	TBD	V	
SAR ADC AC Specifications							
SID106	A_PSRR	Power supply rejection ratio	70	–	–	dB	
SID107	A_CMRR	Common mode rejection ratio	66	–	–	dB	Measured at 1 V
SID108	A_SAMP	Sample rate	–	–	1	Msps	
SID109	A_SNR	Signal-to-noise and distortion ratio (SINAD)	65	–	–	dB	F_{IN} = 10 kHz
SID110	A_BW	Input bandwidth without aliasing	–	–	A_samp/2	kHz	
SID111	A_INL	Integral non linearity. V_{DD} = 1.71 to 5.5, 1 Msps	–1.7	–	2	LSB	V_{REF} = 1 to V_{DD}
SID111A	A_INL	Integral non linearity. V_{DDD} = 1.71 to 3.6, 1 Msps	–1.5	–	1.7	LSB	V_{REF} = 1.71 to V_{DD}
SID111B	A_INL	Integral non linearity. V_{DD} = 1.71 to 5.5, 500 ksps	–1.5	–	1.7	LSB	V_{REF} = 1 to V_{DD}
SID112	A_DNL	Differential non linearity. V_{DD} = 1.71 to 5.5, 1 Msps	–1	_	2.2	LSB	V_{REF} = 1 to V_{DD}
SID112A	A_DNL	Differential non linearity. V_{DD} = 1.71 to 3.6, 1 Msps	–1	_	2	LSB	V_{REF} = 1.71 to V_{DD}
SID112B	A_DNL	Differential non linearity. V_{DD} = 1.71 to 5.5, 500 ksps	–1	_	2.2	LSB	V_{REF} = 1 to V_{DD}
SID113	A_THD	Total harmonic distortion	–	–	–65	dB	Fin = 10 kHz
SID261	FSARINTREF	SAR operating speed without external ref. bypass	_	_	100	ksps	12-bit resolution

Table 19. SPI DC Specifications[9]

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID163	ISPI1	Block current consumption at 1 Mbps	–	–	360	µA	–
SID164	ISPI2	Block current consumption at 4 Mbps	–	–	560		–
SID165	ISPI3	Block current consumption at 8 Mbps	–	–	600		–

Table 20. SPI AC Specifications[8]

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID166	FSPI	SPI Operating frequency (Master; 6X Oversampling)	–	–	8	MHz	SID166
Fixed SPI Master Mode AC Specifications							
SID167	TDMO	MOSI Valid after SClock driving edge	–	–	15	ns	–
SID168	TDSI	MISO Valid before SClock capturing edge	20	–	–		Full clock, late MISO sampling
SID169	THMO	Previous MOSI data hold time	0	–	–		Referred to Slave capturing edge
Fixed SPI Slave Mode AC Specifications							
SID170	TDMI	MOSI Valid before Sclock Capturing edge	40	–	–	ns	–
SID171	TDSO	MISO Valid after Sclock driving edge	–	–	42 + 3*Tcpu		$T_{CPU} = 1/F_{CPU}$
SID171A	TDSO_EXT	MISO Valid after Sclock driving edge in Ext. Clk mode	–	–	48		–
SID172	THSO	Previous MISO data hold time	0	–	–		–
SID172A	TSSELSSCK	SSEL Valid to first SCK Valid edge	–	–	100	ns	–

Table 21. UART DC Specifications[9]

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID160	I_{UART1}	Block current consumption at 100 Kbps	–	–	55	µA	–
SID161	I_{UART2}	Block current consumption at 1000 Kbps	–	–	312	µA	–

Table 22. UART AC Specifications[9]

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID162	F_{UART}	Bit rate	–	–	1	Mbps	–

Table 23. LCD Direct Drive DC Specifications[9]

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID154	I_{LCDLOW}	Operating current in low power mode	–	5	–	µA	16 × 4 small segment disp. at 50 Hz
SID155	C_{LCDCAP}	LCD capacitance per segment/common driver	–	500	5000	pF	–
SID156	LCD_{OFFSET}	Long-term segment offset	–	20	–	mV	–
SID157	I_{LCDOP1}	LCD system operating current Vbias = 5 V	–	2	–	mA	32 × 4 segments. 50 Hz. 25 °C
SID158	I_{LCDOP2}	LCD system operating current Vbias = 3.3 V	–	2	–		32 × 4 segments. 50 Hz. 25 °C

Table 24. LCD Direct Drive AC Specifications[9]

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID159	F_{LCD}	LCD frame rate	10	50	150	Hz	–

Note
9. Guaranteed by characterization.

Memory

Table 25. Flash DC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID173	V_{PE}	Erase and program voltage	1.71	–	5.5	V	–

Table 26. Flash AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID174	$T_{ROWWRITE}$[10]	Row (block) write time (erase and program)	–	–	20	ms	Row (block) = 128 bytes
SID175	$T_{ROWERASE}$[10]	Row erase time	–	–	16		–
SID176	$T_{ROWPROGRAM}$[10]	Row program time after erase	–	–	4		–
SID178	$T_{BULKERASE}$[10]	Bulk erase time (64 KB)	–	–	35		–
SID180[11]	$T_{DEVPROG}$[10]	Total device program time	–	–	7	Seconds	–
SID181[11]	F_{END}	Flash endurance	100 K	–	–	Cycles	–
SID182[11]	F_{RET}	Flash retention. $T_A \leq 55$ °C, 100 K P/E cycles	20	–	–	Years	–
SID182A[11]	–	Flash retention. $T_A \leq 85$ °C, 10 K P/E cycles	10	–	–		–
SID256	TWS48	Number of Wait states at 48 MHz	2	–	–		CPU execution from Flash
SID257	TWS24	Number of Wait states at 24 MHz	1	–	–		CPU execution from Flash

System Resources

Power-on Reset (POR)

Table 27. Power On Reset (PRES)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID.CLK#6	SR_POWER_UP	Power supply slew rate	1	–	67	V/ms	At power-up
SID185[11]	$V_{RISEIPOR}$	Rising trip voltage	0.80	–	1.5	V	–
SID186[11]	$V_{FALLIPOR}$	Falling trip voltage	0.70	–	1.4		–

Table 28. Brown-out Detect (BOD) for V_{CCD}

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID190[11]	$V_{FALLPPOR}$	BOD trip voltage in active and sleep modes	1.48	–	1.62	V	–
SID192[11]	$V_{FALLDPSLP}$	BOD trip voltage in Deep Sleep	1.11	–	1.5		–

Notes
10. It can take as much as 20 milliseconds to write to Flash. During this time the device should not be Reset, or Flash operations will be interrupted and cannot be relied on to have completed. Reset sources include the XRES pin, software resets, CPU lockup states and privilege violations, improper power supply levels, and watchdogs. Make certain that these are not inadvertently activated.
11. Guaranteed by characterization.

SWD Interface

Table 29. SWD Interface Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID213	F_SWDCLK1	3.3 V ≤ V_{DD} ≤ 5.5 V	–	–	14	MHz	SWDCLK ≤ 1/3 CPU clock frequency
SID214	F_SWDCLK2	1.71 V ≤ V_{DD} ≤ 3.3 V	–	–	7		SWDCLK ≤ 1/3 CPU clock frequency
SID215[12]	T_SWDI_SETUP	T = 1/f SWDCLK	0.25*T	–	–	ns	–
SID216[12]	T_SWDI_HOLD	T = 1/f SWDCLK	0.25*T	–	–		–
SID217[12]	T_SWDO_VALID	T = 1/f SWDCLK	–	–	0.5*T		–
SID217A[12]	T_SWDO_HOLD	T = 1/f SWDCLK	1	–	–		–

Internal Main Oscillator

Table 30. IMO DC Specifications

(Guaranteed by Design)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID218	I_{IMO1}	IMO operating current at 48 MHz	–	–	250	µA	–
SID219	I_{IMO2}	IMO operating current at 24 MHz	–	–	180	µA	–

Table 31. IMO AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID223	$F_{IMOTOL1}$	Frequency variation at 24, 32, and 48 MHz (trimmed)	–	–	±2	%	
SID226	$T_{STARTIMO}$	IMO startup time	–	–	7	µs	–
SID228	$T_{JITRMSIMO2}$	RMS jitter at 24 MHz	–	145	–	ps	–

Internal Low-Speed Oscillator

Table 32. ILO DC Specifications

(Guaranteed by Design)

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID231[12]	I_{ILO1}	ILO operating current	–	0.3	1.05	µA	–

Table 33. ILO AC Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID234[12]	$T_{STARTILO1}$	ILO startup time	–	–	2	ms	–
SID236[12]	$T_{ILODUTY}$	ILO duty cycle	40	50	60	%	–
SID237	$F_{ILOTRIM1}$	ILO frequency range	20	40	80	kHz	–

Note
12. Guaranteed by characterization.

Table 34. Watch Crystal Oscillator (WCO) Specifications

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
SID398	FWCO	Crystal Frequency	–	32.768	–	kHz	
SID399	FTOL	Frequency tolerance	–	50	250	ppm	With 20-ppm crystal
SID400	ESR	Equivalent series resistance	–	50	–	kΩ	
SID401	PD	Drive Level	–	–	1	µW	
SID402	TSTART	Startup time	–	–	500	ms	
SID403	CL	Crystal Load Capacitance	6	–	12.5	pF	
SID404	C0	Crystal Shunt Capacitance	–	1.35	–	pF	
SID405	IWCO1	Operating Current (high power mode)	–	–	8	uA	
SID406	IWCO2	Operating Current (low power mode)	–	–	1	uA	

Table 35. External Clock Specifications

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID305[13]	ExtClkFreq	External clock input frequency	0	–	48	MHz	–
SID306[13]	ExtClkDuty	Duty cycle; measured at $V_{DD/2}$	45	–	55	%	–

Table 36. Block Specs

Spec ID	Parameter	Description	Min	Typ	Max	Units	Details/Conditions
SID262[13]	$T_{CLKSWITCH}$	System clock source switching time	3	–	4	Periods	–

Table 37. Smart I/O Pass-through Time (Delay in Bypass Mode)

Spec ID#	Parameter	Description	Min	Typ	Max	Units	Details / Conditions
SID252	PRG_BYPASS	Max delay added by Smart I/O in bypass mode	–	–	1.6	ns	

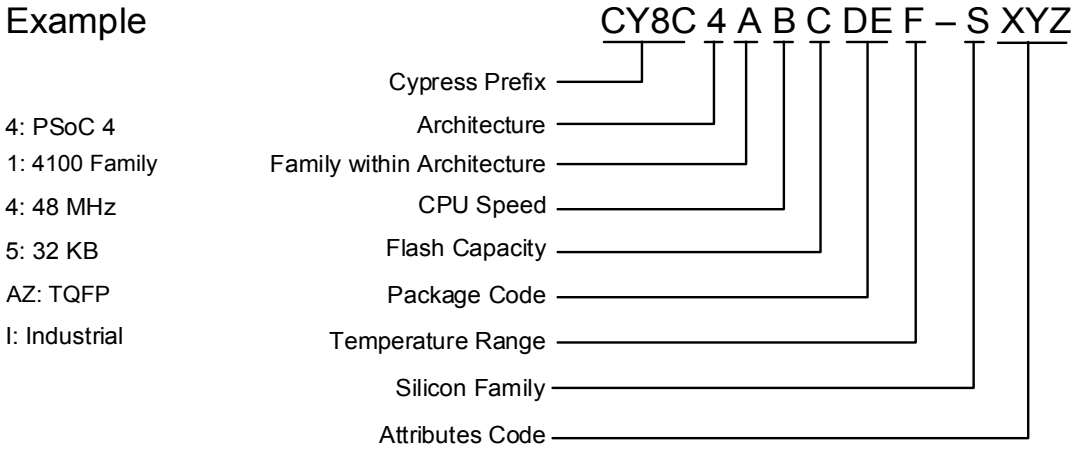
Note
13. Guaranteed by characterization.

The nomenclature used in the preceding table is based on the following part numbering convention:

Field	Description	Values	Meaning
CY8C	Cypress Prefix		
4	Architecture	4	PSoC 4
A	Family	1	4100 Family
B	CPU Speed	2	24 MHz
		4	48 MHz
C	Flash Capacity	4	16 KB
		5	32 KB
		6	64 KB
		7	128 KB
DE	Package Code	AX	TQFP (0.8mm pitch)
		AZ	TQFP (0.5mm pitch)
		LQ	QFN
		PV	SSOP
		FN	CSP
F	Temperature Range	I	Industrial
S	Silicon Family	S	PSoC 4A-S1, PSoC 4A-S2
		M	PSoC 4A-M
		L	PSoC 4A-L
		BL	PSoC 4A-BLE
XYZ	Attributes Code	000-999	Code of feature set in the specific family

The following is an example of a part number:

Example



Packaging

The PSoC 4100S will be offered in 48-pin TQFP, 44-pin TQFP, 40-pin QFN, 32-pin QFN, and 35-ball WLCSP packages. Package dimensions and Cypress drawing numbers are in the following table.

Table 38. Package List

Spec ID#	Package	Description	Package Dwg
BID20	48-pin TQFP	7 × 7 × 1.4-mm height with 0.5-mm pitch	51-85135
BID20A	44-pin TQFP	10 × 10 × 1.6-mm height with 0.8-mm pitch	51-85064
BID27	40-pin QFN	6 × 6 × 0.6-mm height with 0.5-mm pitch	001-80659
BID34A	32-pin QFN	5 × 5 × 0.6-mm height with 0.5-mm pitch	001-42168
BID34D	35-ball WLCSP	2.6 × 2.1 × 0.48-mm height with 0.35-mm pitch	002-09958

Table 39. Package Thermal Characteristics

Parameter	Description	Package	Min	Typ	Max	Units
T_A	Operating Ambient temperature		–40	25	85	°C
T_J	Operating junction temperature		–40	–	100	°C
T_{JA}	Package θ_{JA}	48-pin TQFP	–	74.8	–	°C/Watt
T_{JC}	Package θ_{JC}	48-pin TQFP	–	35.7	–	°C/Watt
T_{JA}	Package θ_{JA}	44-pin TQFP	–	57.2	–	°C/Watt
T_{JC}	Package θ_{JC}	44-pin TQFP	–	17.5	–	°C/Watt
T_{JA}	Package θ_{JA}	40-pin QFN	–	17.8	–	°C/Watt
T_{JC}	Package θ_{JC}	40-pin QFN	–	2.8	–	°C/Watt
T_{JA}	Package θ_{JA}	32-pin QFN	–	19.9	–	°C/Watt
T_{JC}	Package θ_{JC}	32-pin QFN	–	4.3	–	°C/Watt
T_{JA}	Package θ_{JA}	35-ball WLCSP	–	43	–	°C/Watt
T_{JC}	Package θ_{JC}	35-ball WLCSP	–	0.3	–	°C/Watt

Table 40. Solder Reflow Peak Temperature

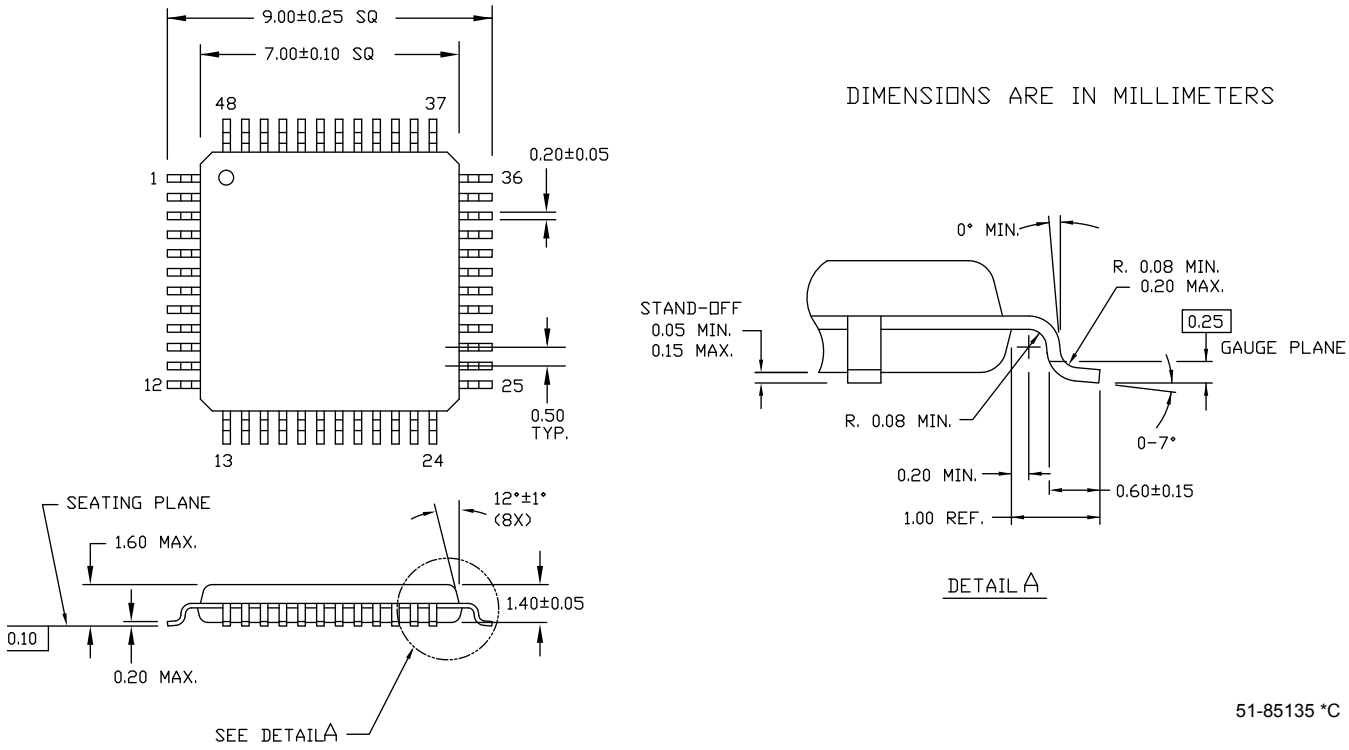
Package	Maximum Peak Temperature	Maximum Time at Peak Temperature
All	260 °C	30 seconds

Table 41. Package Moisture Sensitivity Level (MSL), IPC/JEDEC J-STD-020

Package	MSL
All except WLCSP	MSL 3
35-ball WLCSP	MSL 1

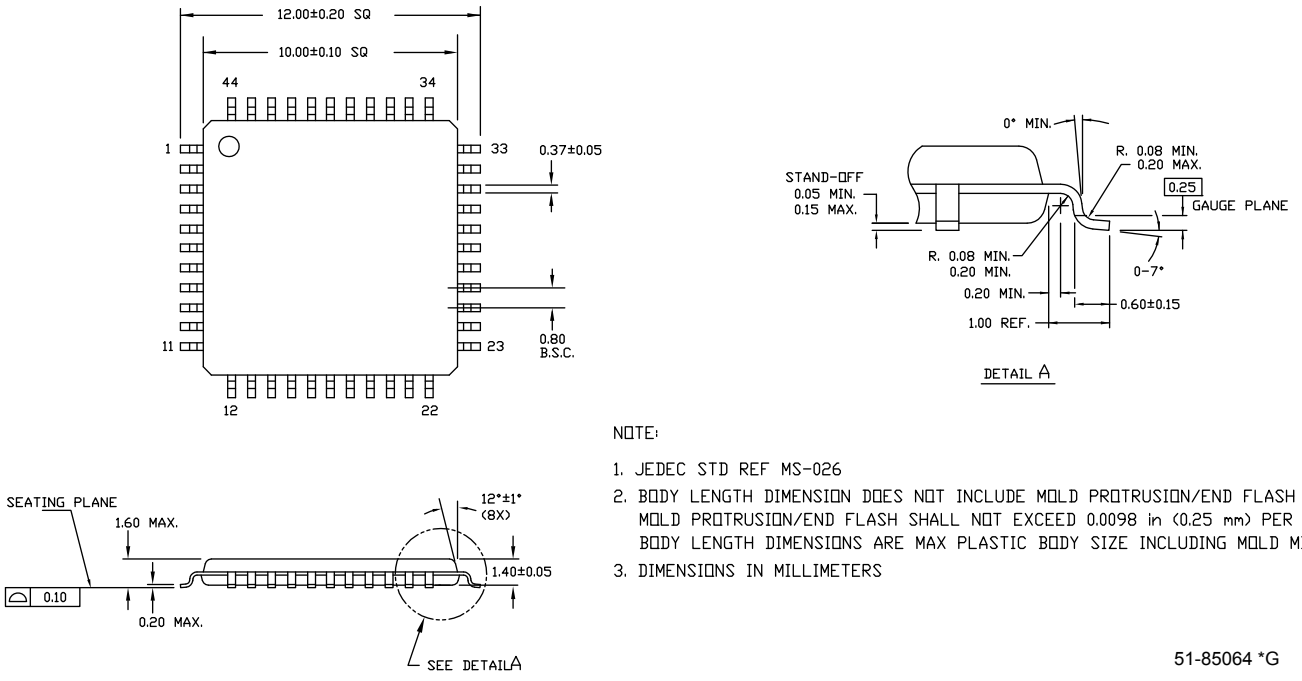
Package Diagrams

Figure 6. 48-pin TQFP Package Outline



51-85135 *C

Figure 7. 44-pin TQFP Package Outline

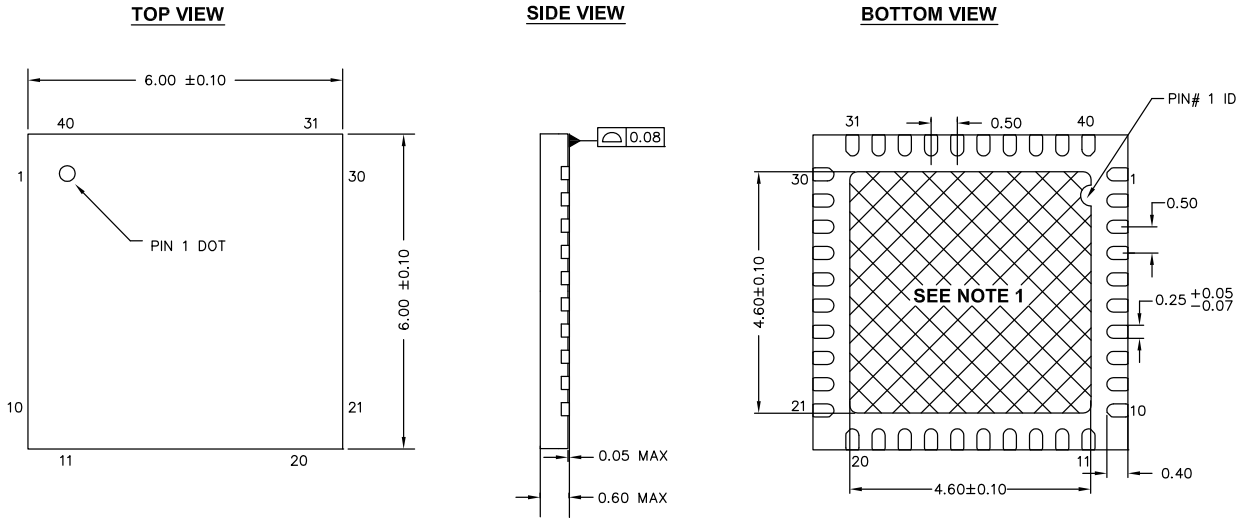


NOTE:

1. JEDEC STD REF MS-026
2. BODY LENGTH DIMENSION DOES NOT INCLUDE MOLD PROTRUSION/END FLASH
   MOLD PROTRUSION/END FLASH SHALL NOT EXCEED 0.0098 in (0.25 mm) PER SIDE
   BODY LENGTH DIMENSIONS ARE MAX PLASTIC BODY SIZE INCLUDING MOLD MISMATCH
3. DIMENSIONS IN MILLIMETERS

51-85064 *G

Figure 8. 40-pin QFN Package Outline

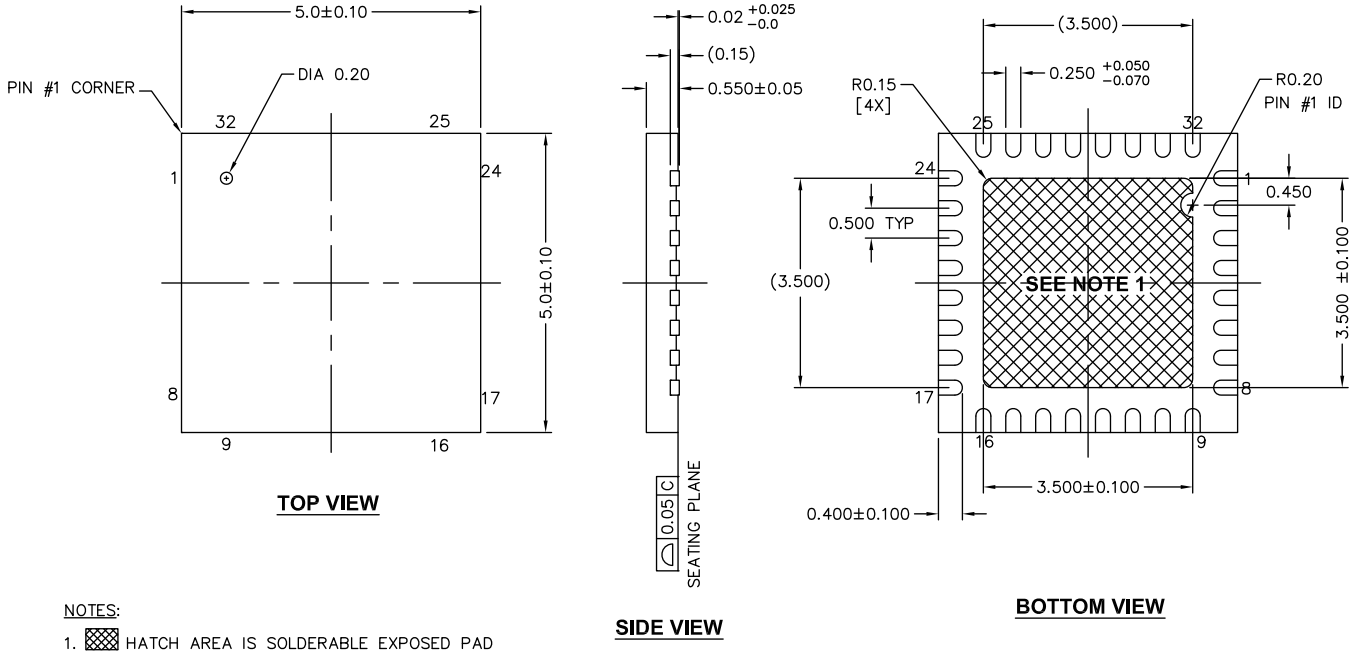


NOTES:

1. HATCH AREA IS SOLDERABLE EXPOSED PAD
2. REFERENCE JEDEC # MO-248
3. PACKAGE WEIGHT: 68 ±2 mg
4. ALL DIMENSIONS ARE IN MILLIMETERS

001-80659 *A

Figure 9. 32-pin QFN Package Outline

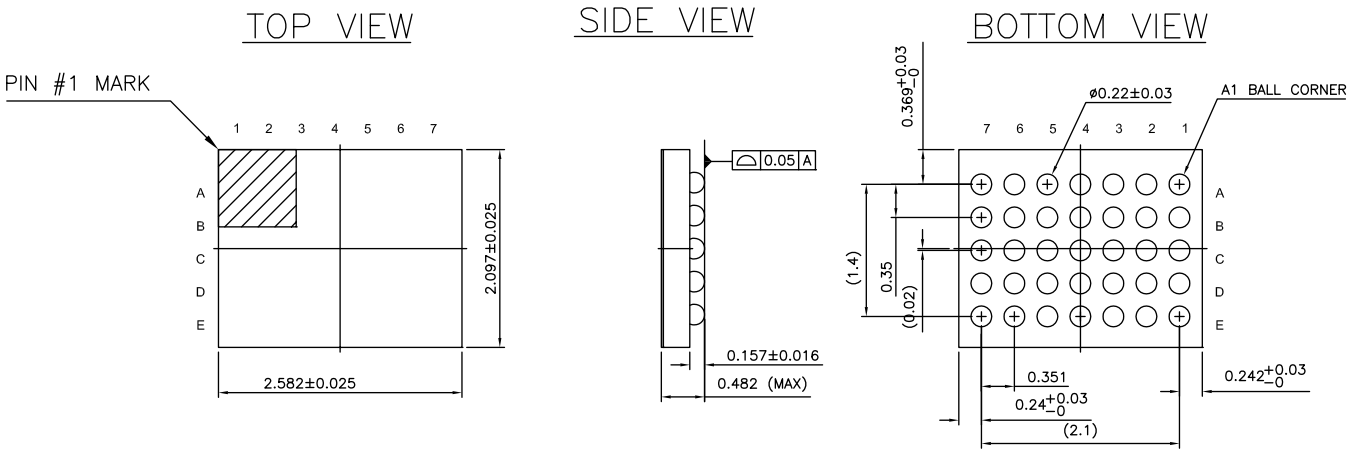


NOTES:

1. HATCH AREA IS SOLDERABLE EXPOSED PAD
2. BASED ON REF JEDEC # MO−248
3. PACKAGE WEIGHT: 0.0388g
4. DIMENSIONS ARE IN MILLIMETERS

001-42168 *E

Figure 10. 35-Ball WLCSP Package Outline



ALL DIMENSIONS ARE IN MM
JEDEC Publication 95; Design Guide 4.18

002-09958 *C

Table 42. Acronyms Used in this Document *(continued)*

Acronym	Description
PC	program counter
PCB	printed circuit board
PGA	programmable gain amplifier
PHUB	peripheral hub
PHY	physical layer
PICU	port interrupt control unit
PLA	programmable logic array
PLD	programmable logic device, see also PAL
PLL	phase-locked loop
PMDD	package material declaration data sheet
POR	power-on reset
PRES	precise power-on reset
PRS	pseudo random sequence
PS	port read data register
PSoC®	Programmable System-on-Chip™
PSRR	power supply rejection ratio
PWM	pulse-width modulator
RAM	random-access memory
RISC	reduced-instruction-set computing
RMS	root-mean-square
RTC	real-time clock
RTL	register transfer language
RTR	remote transmission request
RX	receive
SAR	successive approximation register
SC/CT	switched capacitor/continuous time
SCL	I^2C serial clock
SDA	I^2C serial data
S/H	sample and hold
SINAD	signal to noise and distortion ratio
SIO	special input/output, GPIO with advanced features. See GPIO.
SOC	start of conversion
SOF	start of frame
SPI	Serial Peripheral Interface, a communications protocol
SR	slew rate
SRAM	static random access memory
SRES	software reset
SWD	serial wire debug, a test protocol

Table 42. Acronyms Used in this Document *(continued)*

Acronym	Description
SWV	single-wire viewer
TD	transaction descriptor, see also DMA
THD	total harmonic distortion
TIA	transimpedance amplifier
TRM	technical reference manual
TTL	transistor-transistor logic
TX	transmit
UART	Universal Asynchronous Transmitter Receiver, a communications protocol
UDB	universal digital block
USB	Universal Serial Bus
USBIO	USB input/output, PSoC pins used to connect to a USB port
VDAC	voltage DAC, see also DAC, IDAC
WDT	watchdog timer
WOL	write once latch, see also NVL
WRES	watchdog timer reset
XRES	external reset I/O pin
XTAL	crystal

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